

D J Wallis

List of Publications by Year in descending order

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33
papers

854
citations

623734

14
h-index

477307

29
g-index

33
all docs

33
docs citations

33
times ranked

1168
citing authors

#	ARTICLE	IF	CITATIONS
1	Method for inferring the mechanical strain of GaN-on-Si epitaxial layers using optical profilometry and finite element analysis. <i>Optical Materials Express</i> , 2021, 11, 1643.	3.0	7
2	Photoluminescence efficiency of zincblende InGaN/GaN quantum wells. <i>Journal of Applied Physics</i> , 2021, 129, .	2.5	9
3	The effect of thermal annealing on the optical properties of Mg-doped zincblende GaN epilayers. <i>Journal of Applied Physics</i> , 2021, 130, .	2.5	3
4	Alloy segregation at stacking faults in zincblende GaN heterostructures. <i>Journal of Applied Physics</i> , 2020, 128, 145703.	2.5	8
5	Stacking fault-associated polarized surface-emitted photoluminescence from zincblende InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	6
6	High-Performance MMIC Inductors for GaN-on-Low-Resistivity Silicon for Microwave Applications. <i>IEEE Microwave and Wireless Components Letters</i> , 2018, 28, 99-101.	3.2	10
7	Effect of stacking faults on the photoluminescence spectrum of zincblende GaN. <i>Journal of Applied Physics</i> , 2018, 123, .	2.5	10
8	Low-Loss MMICs Viable Transmission Media for GaN-on-Low Resistivity Silicon Technology. <i>IEEE Microwave and Wireless Components Letters</i> , 2017, 27, 10-12.	3.2	8
9	Photoluminescence studies of cubic GaN epilayers. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1600733.	1.5	16
10	InGaN μ LEDs integrated onto colloidal quantum dot functionalized ultra-thin glass. <i>Optics Express</i> , 2017, 25, 19179.	3.4	12
11	Terahertz monolithic integrated circuits (TMICs) array antenna technology on GaN-on-Low resistivity silicon substrates. , 2016, , .		9
12	Integrated dual-color InGaN light-emitting diode array through transfer printing. , 2015, , .		2
13	High Performance GaN High Electron Mobility Transistors on Low Resistivity Silicon for π -Band Applications. <i>IEEE Electron Device Letters</i> , 2015, 36, 899-901.	3.9	25
14	Heterogeneous integration of gallium nitride light-emitting diodes on diamond and silica by transfer printing. <i>Optics Express</i> , 2015, 23, 9329.	3.4	57
15	Novel Shielded Coplanar Waveguides on GaN-on-Low Resistivity Si Substrates for MMIC Applications. <i>IEEE Microwave and Wireless Components Letters</i> , 2015, 25, 427-429.	3.2	12
16	Measuring the composition of AlGaIn layers in GaN based structures grown on 150 mm Si substrates using $(2\pi/a)$ reciprocal space maps. <i>Semiconductor Science and Technology</i> , 2013, 28, 094006.	2.0	23
17	Prospects of III-nitride optoelectronics grown on Si. <i>Reports on Progress in Physics</i> , 2013, 76, 106501.	20.1	249
18	Origin of kink effect in AlGaIn/GaN high electron mobility transistors: Yellow luminescence and Fe doping. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	15

#	ARTICLE	IF	CITATIONS
19	GaN-based LEDs grown on 6-inch diameter Si (111) substrates by MOVPE. Proceedings of SPIE, 2009, , .	0.8	41
20	Time-Resolved Temperature Measurement of AlGaIn/GaN Electronic Devices Using Micro-Raman Spectroscopy. IEEE Electron Device Letters, 2007, 28, 86-89.	3.9	114
21	Time-resolved nanosecond sub-micron resolution thermal analysis of high-power AlGaIn/GaN HFETs. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2014-2018.	1.8	2
22	Control of Short-Channel Effects in GaN/AlGaIn HFETs. , 2006, , .		24
23	On the incorporation mechanism of Fe in GaN grown by metal-organic vapour phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1429-1434.	0.8	26
24	Z-contrast imaging of AlN exclusion layers in GaN field-effect transistors. Applied Physics Letters, 2005, 87, 042101.	3.3	7
25	Thermal mapping of defects in AlGaIn ^x GaN heterostructure field-effect transistors using micro-Raman spectroscopy. Applied Physics Letters, 2005, 87, 103508.	3.3	34
26	Composition measurement in strained AlGaIn epitaxial layers using x-ray diffraction. Applied Physics Letters, 2004, 85, 6359-6361.	3.3	12
27	Analysis of thin AlN carrier exclusion layers in AlGaIn/GaN microwave heterojunction field-effect transistors. Semiconductor Science and Technology, 2004, 19, L65-L67.	2.0	28
28	AlGaIn/GaN microwave HFET including a thin AlN carrier exclusion layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2331-2334.	0.8	23
29	Mosaic Crystal Tilts and Their Relationship to Dislocation Structure, Surface Roughness and Growth Conditions in Relaxed SiGe Layers. Materials Research Society Symposia Proceedings, 1998, 533, 77.	0.1	4
30	High-mobility two-dimensional electron gases in Si/SiGe heterostructures on relaxed SiGe layers grown at high temperature. Semiconductor Science and Technology, 1997, 12, 943-946.	2.0	36
31	A Combined-Techniques Approach to Elucidating Crystalline Interface Atomic Structure. Materials Research Society Symposia Proceedings, 1996, 466, 45.	0.1	0
32	Analysis of nanometre-sized pyrogenic particles in the scanning transmission electron microscope. Journal of Microscopy, 1996, 184, 185-194.	1.8	18
33	Synthesis and Properties of GaAs Nanocrystals in SiO ₂ Formed by Ion Implantation. Materials Research Society Symposia Proceedings, 1995, 396, 447.	0.1	4